

Title (en)

Nonvolatile semiconductor memory devices

Title (de)

Nichtflüchtige Halbleiterspeichervorrichtungen

Title (fr)

Dispositifs de mémoire à semi-conducteurs non volatile

Publication

**EP 1830364 A1 20070905 (EN)**

Application

**EP 07109268 A 20020130**

Priority

- EP 02250636 A 20020130
- JP 2001262882 A 20010831

Abstract (en)

A nonvolatile semiconductor memory device including a plurality of digit lines (GBL) to which a plurality of nonvolatile memory cells (MC) are connected, wherein the digit lines include a first digit line (GBL) to which a selected one of the nonvolatile memory cells (MC) is connected; and a second digit line (GBL) to which only non-selected nonvolatile memory cells (MC) are connected, the nonvolatile semiconductor memory device further comprising a selecting portion (SS) provided for every predetermined number of the digit lines (GBL) and for, upon reading memory cell information, selecting both the first and second digit lines (GBL) and, upon writing memory cell information, selecting only the first digit line (GBL).

IPC 8 full level

**G11C 7/18** (2006.01); **G11C 16/04** (2006.01); **G11C 16/06** (2006.01); **G11C 16/24** (2006.01); **G11C 16/28** (2006.01)

CPC (source: EP KR US)

**G11C 7/18** (2013.01 - EP US); **G11C 16/06** (2013.01 - KR); **G11C 16/24** (2013.01 - EP US); **G11C 16/28** (2013.01 - EP US)

Citation (search report)

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Designated contracting state (EPC)

DE FR GB IT

DOCDB simple family (publication)

**EP 1288965 A2 20030305; EP 1288965 A3 20060621;** CN 100576351 C 20091230; CN 1197163 C 20050413; CN 1404156 A 20030319; CN 1655282 A 20050817; DE 60230345 D1 20090122; DE 60239899 D1 20110609; EP 1826775 A1 20070829; EP 1826775 B1 20110907; EP 1826776 A1 20070829; EP 1826776 B1 20110427; EP 1830364 A1 20070905; EP 1830364 B1 20081210; EP 1830365 A1 20070905; JP 2003077282 A 20030314; KR 100689738 B1 20070309; KR 20030019056 A 20030306; TW 552583 B 20030911; US 2003043623 A1 20030306; US 6917541 B2 20050712

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